

<IGBT Modules>

CM200DY-13T

 HIGH POWER SWITCHING USE
INSULATED TYPE


dual switch (half-bridge)

Collector current I_C	2 0 0 A
Collector-emitter voltage V_{CES}	6 5 0 V
Maximum junction temperature T_{vjmax}	1 7 5 °C
<ul style="list-style-type: none"> •dual switch (half-bridge) •Nickel-plating tab terminals •RoHS Directive compliant •UL Recognized under UL1557, File No. E323585 	

APPLICATION

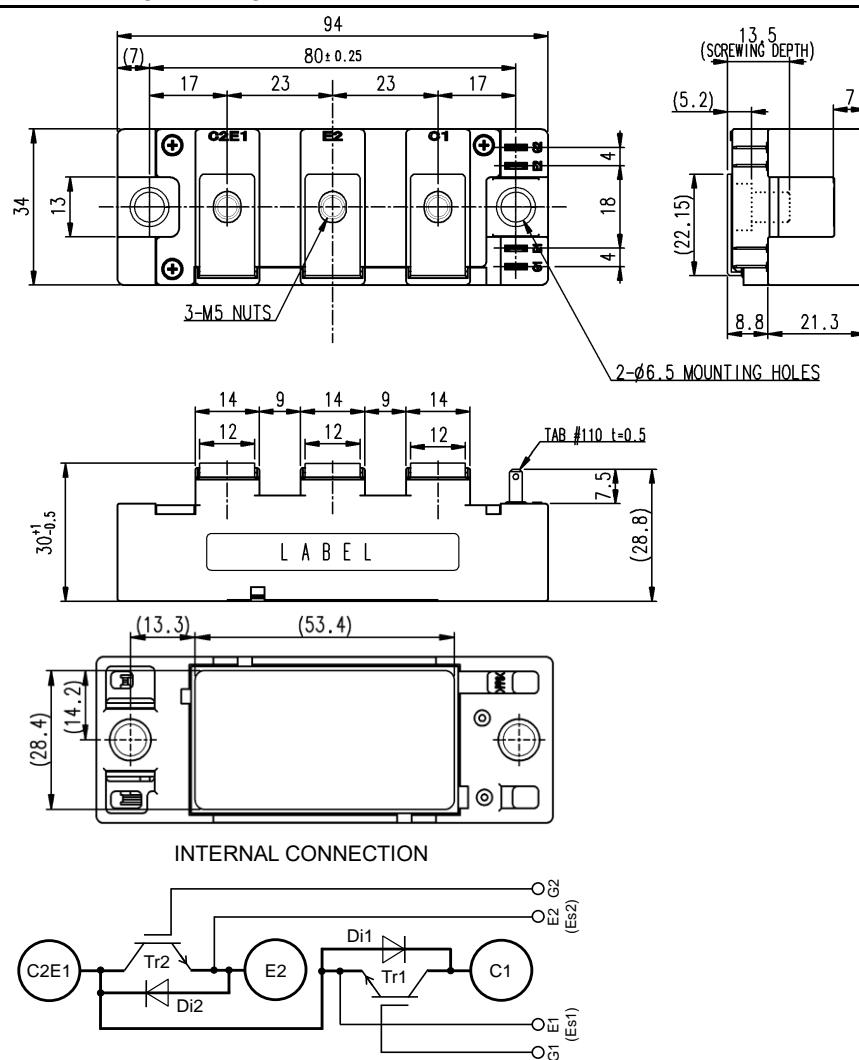
AC Motor Control, Motion/Servo Control, Power supply, etc.

OPTION (Below options are available.)

- PC-TIM (Phase Change Thermal Interface Material) pre-apply ^(Note8)
- V_{CEsat} selection for parallel connection

OUTLINE DRAWING & INTERNAL CONNECTION

Dimension in mm



Tolerance otherwise specified		
Division of Dimension	Tolerance	
0.5	to	3
over 3	to	6
over 6	to	30
over 30	to	120
over 120	to	400
		±0.2
		±0.3
		±0.5
		±0.8
		±1.2

JIS B 0405 c

MAXIMUM RATINGS ($T_{vj}=25^{\circ}\text{C}$, unless otherwise specified)

Symbol	Item	Conditions	Rating	Unit
V_{CES}	Collector-emitter voltage	G-E short-circuited	650	V
V_{GES}	Gate-emitter voltage	C-E short-circuited	± 20	V
I_c	Collector current	DC, $T_c=139^{\circ}\text{C}$ * (Note2, 4)	200	A
I_{CRM}		Pulse, Repetitive (Note3)	400	
P_{tot}	Total power dissipation	$T_c=25^{\circ}\text{C}$ (Note2, 4)	1400	W
I_E (Note1)	Emitter current	DC (Note2)	200	A
I_{ERM} (Note1)		Pulse, Repetitive (Note3)	400	
V_{isol}	Isolation voltage	Terminals to base plate, RMS, $f=60\text{ Hz}$, AC 1 min	4000	V
T_{vjmax}	Maximum junction temperature	Instantaneous event (overload) (Note8)	175	$^{\circ}\text{C}$
T_{Cmax}	Maximum case temperature	(Note4, 8)	150*	
T_{vjop}	Operating junction temperature	Continuous operation (under switching) (Note8)	-40 ~ +150	$^{\circ}\text{C}$
T_{stg}	Storage temperature	-	-40 ~ +150*	

ELECTRICAL CHARACTERISTICS ($T_{vj}=25^{\circ}\text{C}$, unless otherwise specified)

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
I_{CES}	Collector-emitter cut-off current	$V_{CE}=V_{CES}$, G-E short-circuited	-	-	1.0	mA
I_{GES}	Gate-emitter leakage current	$V_{GE}=V_{GES}$, C-E short-circuited	-	-	0.5	μA
$V_{GE(th)}$	Gate-emitter threshold voltage	$I_c=20\text{ mA}$, $V_{CE}=10\text{ V}$	5.4	6.0	6.6	V
V_{CEsat} (Terminal)	Collector-emitter saturation voltage	$I_c=200\text{ A}$, $V_{GE}=15\text{ V}$, Refer to the figure of test circuit (Note5)	$T_{vj}=25^{\circ}\text{C}$	-	1.40	1.70
			$T_{vj}=125^{\circ}\text{C}$	-	1.50	-
			$T_{vj}=150^{\circ}\text{C}$	-	1.55	-
V_{CEsat} (Chip)		$I_c=200\text{ A}$, $V_{GE}=15\text{ V}$, (Note5)	$T_{vj}=25^{\circ}\text{C}$	-	1.30	1.55
			$T_{vj}=125^{\circ}\text{C}$	-	1.35	-
			$T_{vj}=150^{\circ}\text{C}$	-	1.35	-
C_{ies}	Input capacitance	$V_{CE}=10\text{ V}$, G-E short-circuited	-	-	26.7	nF
C_{oes}	Output capacitance		-	-	1.1	
C_{res}	Reverse transfer capacitance		-	-	0.5	
Q_G	Gate charge	$V_{CC}=300\text{ V}$, $I_c=200\text{ A}$, $V_{GE}=15\text{ V}$	-	0.83	-	μC
$t_{d(on)}$	Turn-on delay time	$V_{CC}=300\text{ V}$, $I_c=200\text{ A}$, $V_{GE}=\pm 15\text{ V}$, $R_G=0.47\text{ }\Omega$, Inductive load	-	-	400	ns
t_r	Rise time		-	-	200	
$t_{d(off)}$	Turn-off delay time		-	-	400	
t_f	Fall time		-	-	400	
V_{EC} (Note.1) (Terminal)	Emitter-collector voltage	$I_E=200\text{ A}$, G-E short-circuited, Refer to the figure of test circuit (Note5)	$T_{vj}=25^{\circ}\text{C}$	-	2.10	2.90
			$T_{vj}=125^{\circ}\text{C}$	-	2.05	-
			$T_{vj}=150^{\circ}\text{C}$	-	2.05	-
V_{EC} (Note.1) (Chip)		$I_E=200\text{ A}$, G-E short-circuited, (Note5)	$T_{vj}=25^{\circ}\text{C}$	-	1.90	2.65
			$T_{vj}=125^{\circ}\text{C}$	-	1.80	-
			$T_{vj}=150^{\circ}\text{C}$	-	1.80	-
t_{rr} (Note1)	Reverse recovery time	$V_{CC}=300\text{ V}$, $I_E=200\text{ A}$, $V_{GE}=\pm 15\text{ V}$, $R_G=0.47\text{ }\Omega$, Inductive load	-	-	200	ns
Q_{rr} (Note1)	Reverse recovery charge		-	7.0	-	μC
E_{on}	Turn-on switching energy per pulse	$V_{CC}=300\text{ V}$, $I_c=I_E=200\text{ A}$, $V_{GE}=\pm 15\text{ V}$, $R_G=0.47\text{ }\Omega$, $T_{vj}=150^{\circ}\text{C}$, Inductive load	-	3.1	-	mJ
E_{off}	Turn-off switching energy per pulse		-	10.8	-	
E_{rr} (Note1)	Reverse recovery energy per pulse		-	4.6	-	
$R_{CC'+EE'}$	Internal lead resistance	Main terminals-chip, per switch, $T_c=25^{\circ}\text{C}$ (Note4)	-	0.2	-	$\text{m}\Omega$
r_g	Internal gate resistance	Per switch	-	3.0	-	Ω

*: The value of PC-TIM applied module is limited by the heat resistant temperature of PC-TIM.

THERMAL RESISTANCE CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit	
			Min.	Typ.	Max.		
$R_{th(j-c)Q}$	Thermal resistance	Junction to case, per Inverter IGBT ^(Note4)	-	-	107	K/kW	
$R_{th(j-c)D}$		Junction to case, per Inverter FWD ^(Note4)	-	-	168		
$R_{th(c-s)}$	Contact thermal resistance	Case to heat sink, per 1 module	Thermal grease applied ^(Note4,6,8)	-	36.6	-	K/kW

MECHANICAL CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit	
			Min.	Typ.	Max.		
M_t	Mounting torque	Main terminals	M 5 screw	2.5	3.0	3.5	N·m
M_s	Mounting torque	Mounting to heat sink	M 6 screw	3.5	4.0	4.5	N·m
d_s	Creepage distance	Terminal to terminal		18.4	-	-	mm
		Terminal to base plate		21.1	-	-	
d_a	Clearance	Terminal to terminal		9.6	-	-	mm
		Terminal to base plate		16.7	-	-	
e_c	Flatness of base plate	On the centerline ^(Note7)		± 0	-	+200	μm
m	mass	-		-	120	-	g

*. This product is compliant with the Restriction of the Use of Certain Hazardous Substances in Electrical and Electronic Equipment (RoHS) directive 2011/65/EU and (EU) 2015/863.

Note1. Represent ratings and characteristics of the anti-parallel, emitter-collector free-wheeling diode (FWD).

2. Junction temperature (T_{vj}) should not increase beyond $T_{vj\max}$ rating.

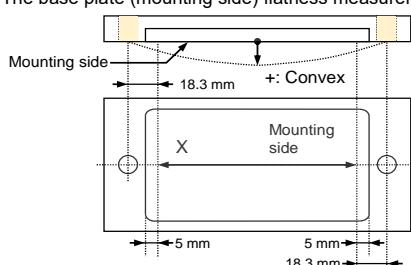
3. Pulse width and repetition rate should be such that the device junction temperature (T_{vj}) dose not exceed $T_{vj\max}$ rating.

4. Case temperature (T_c) and heat sink temperature (T_s) are defined on the each surface (mounting side) of base plate and heat sink just under the chips. Refer to the figure of chip location.

5. Pulse width and repetition rate should be such as to cause negligible temperature rise. Refer to the figure of test circuit.

6. Typical value is measured by using thermally conductive grease of $\lambda=3.0 \text{ W}/(\text{m}\cdot\text{K})/D_{(C-S)}=50 \mu\text{m}$.

7. The base plate (mounting side) flatness measurement point is as follows of the following figure.



8. Long term performance related to thermal conductive grease and PC-TIM (including but not limited to aspects such as the increase of thermal resistance due to pumping out, etc.) should be verified under your specific application conditions. Each temperature condition ($T_{vj\max}$, $T_{vj\text{op}}$, $T_{C\max}$) must be maintained below the maximum rated temperature throughout consideration of the temperature rise even for long term usage.

CM200DY-13T

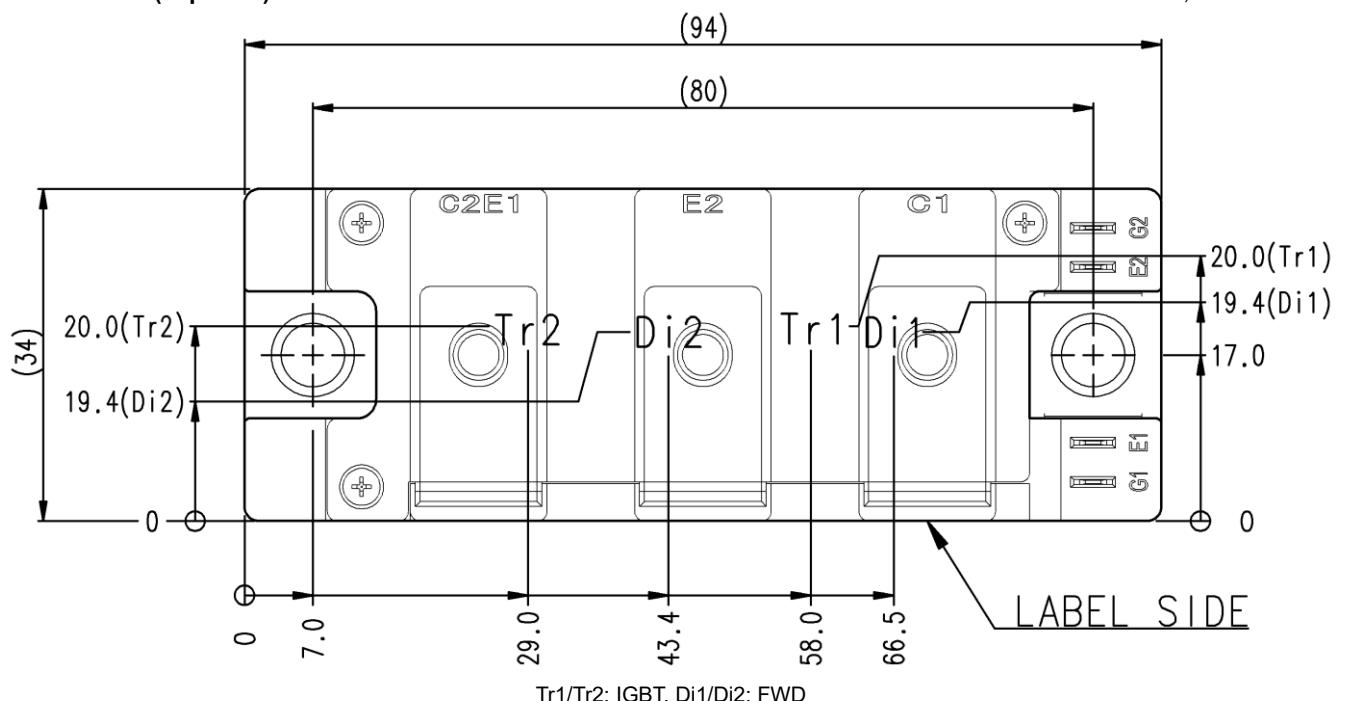
HIGH POWER SWITCHING USE INSULATED TYPE

RECOMMENDED OPERATING CONDITIONS

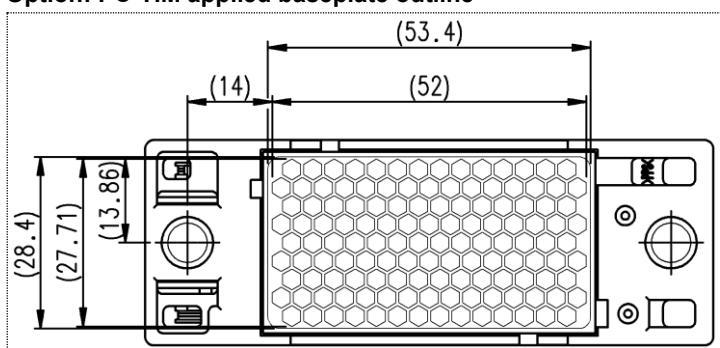
Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
V_{CC}	(DC) Supply voltage	Applied across C1-E2 terminals	-	300	450	V
V_{GEon}	Gate (-emitter drive) voltage	Applied across G1-Es1/G2-Es2 terminals	13.5	15.0	16.5	V
R_G	External gate resistance	Per switch	0.47	-	33	Ω

CHIP LOCATION (Top view)

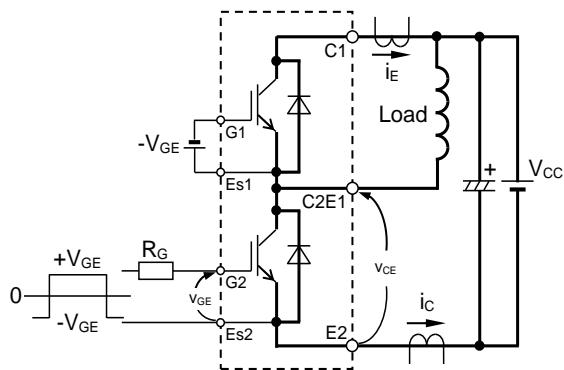
Dimension in mm, tolerance: ± 1 mm



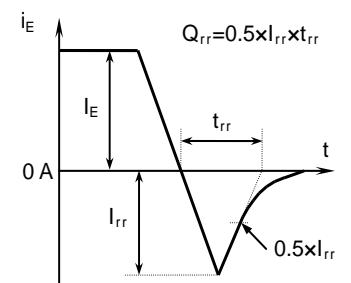
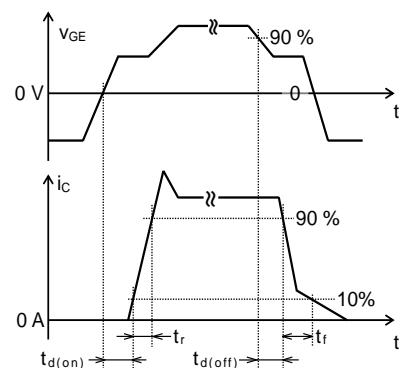
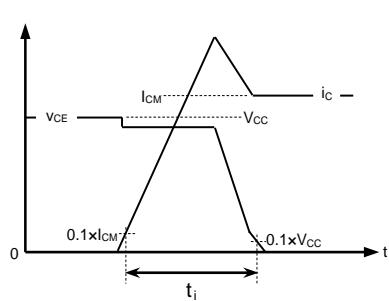
Option: PC-TIM applied baseplate outline



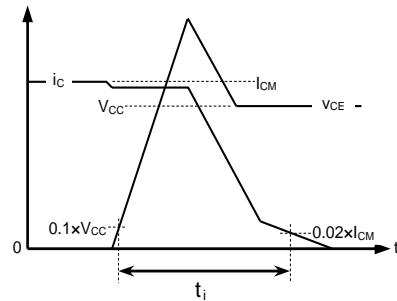
TEST CIRCUIT AND WAVEFORMS



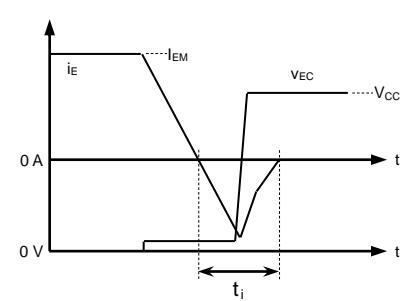
Switching characteristics test circuit and waveforms

t_{rr}, Q_{rr} characteristics test waveform

IGBT Turn-on switching energy



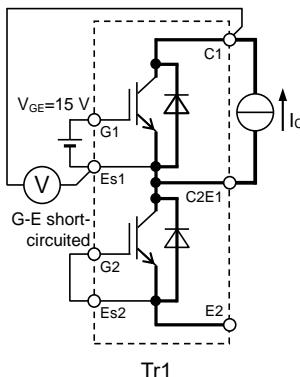
IGBT Turn-off switching energy



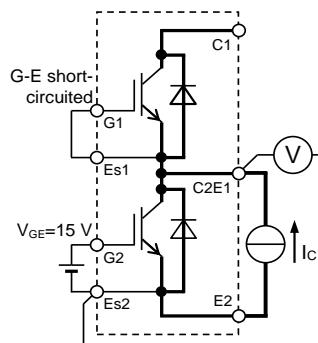
FWD Reverse recovery energy

Turn-on / Turn-off switching energy and Reverse recovery energy test waveforms (Integral time instruction drawing)

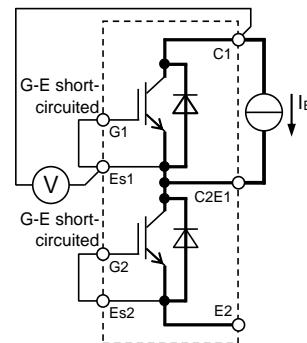
TEST CIRCUIT



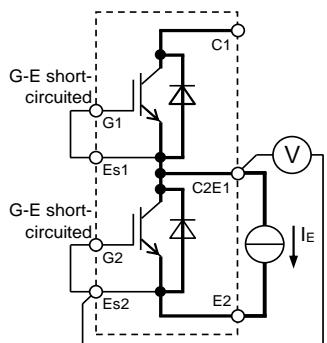
Tr1

V_{CEsat} characteristics test circuit

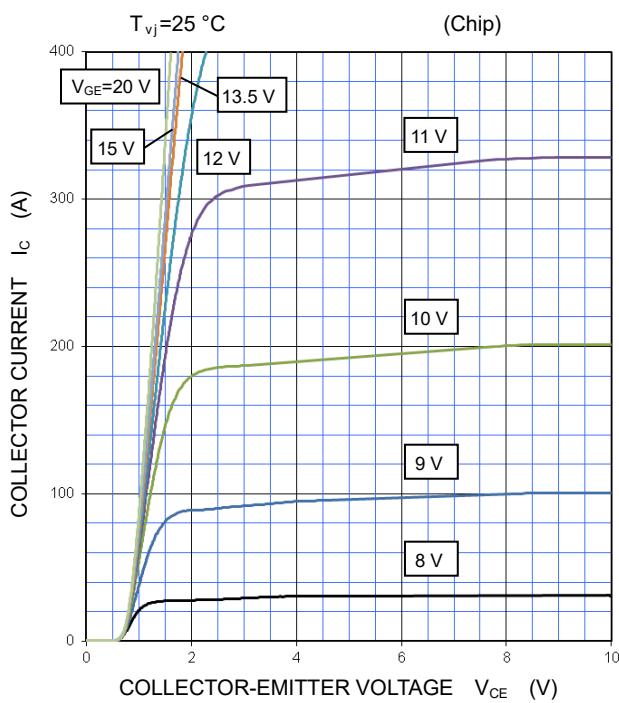
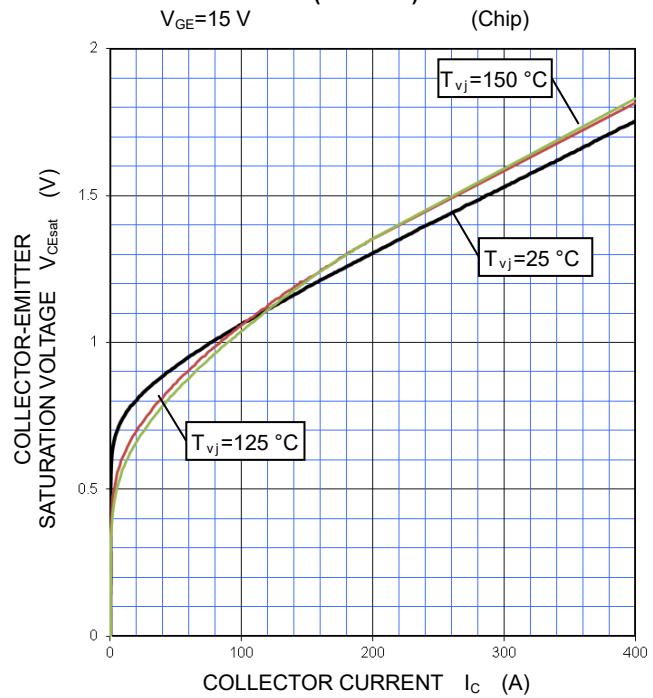
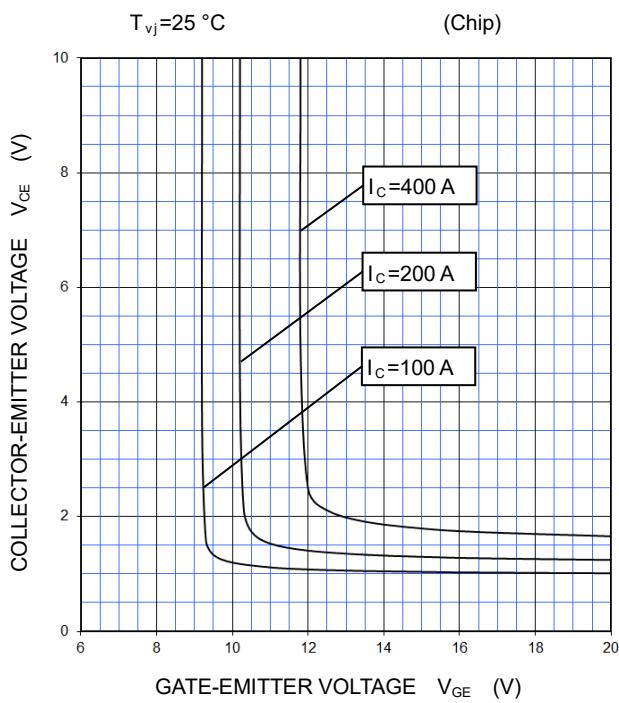
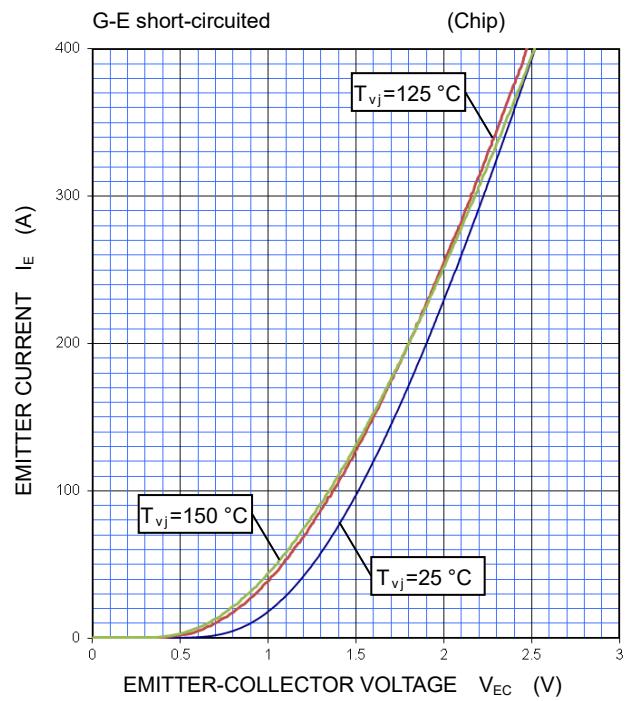
Tr2

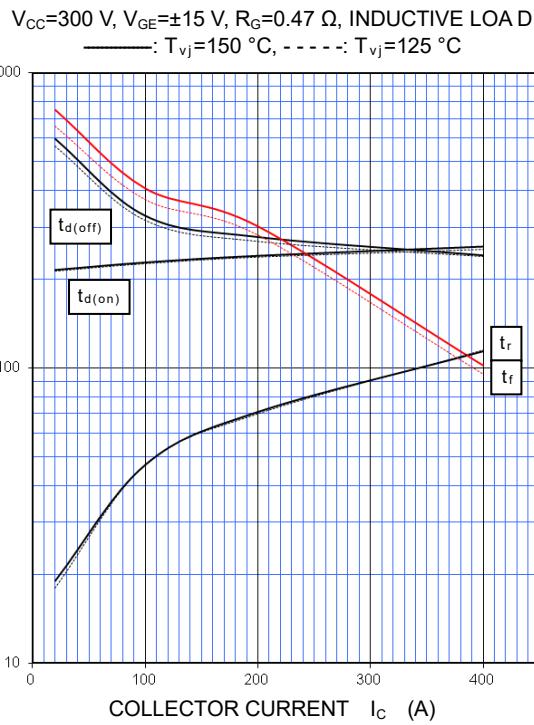
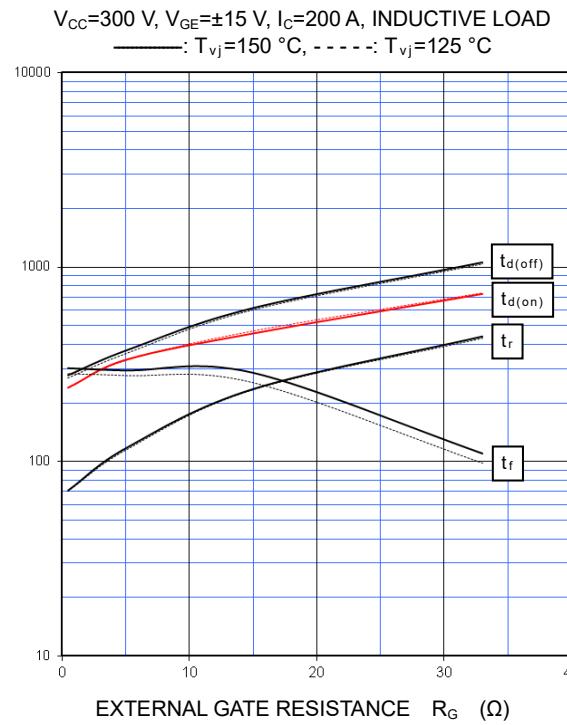
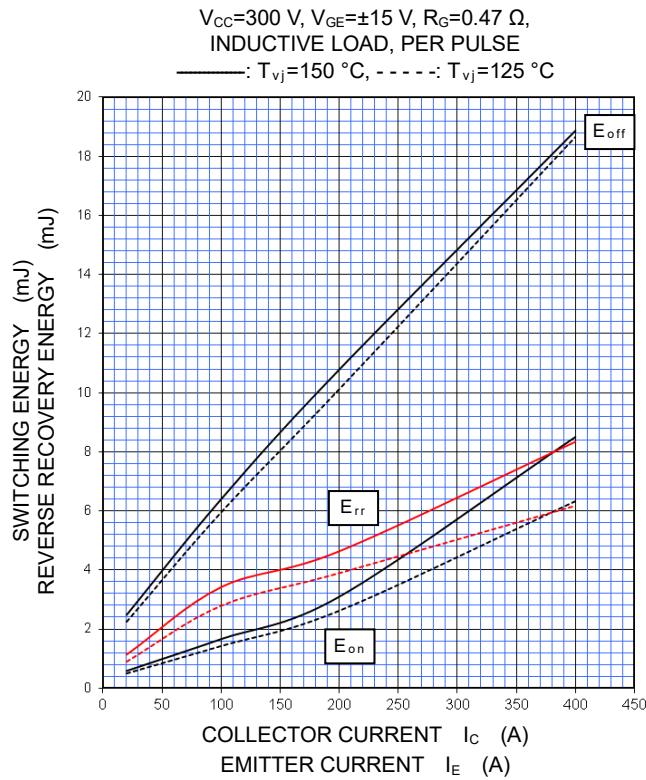
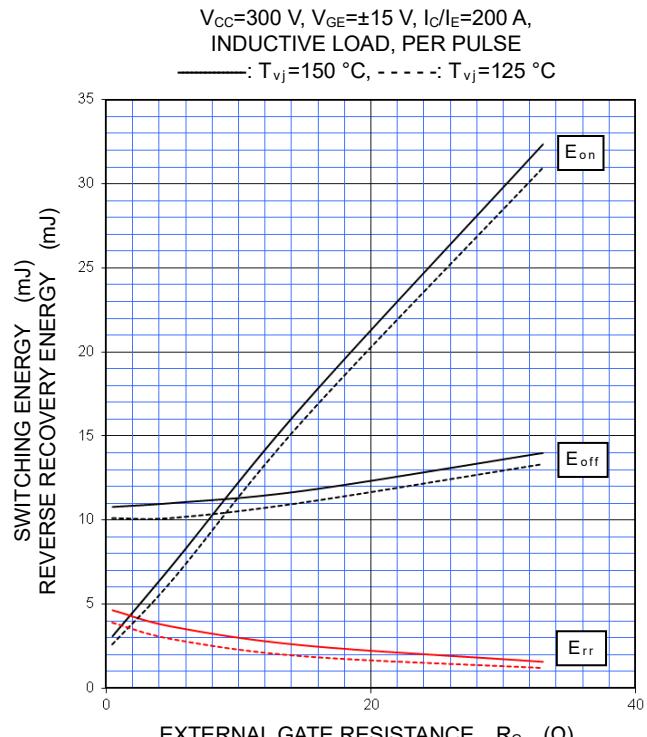


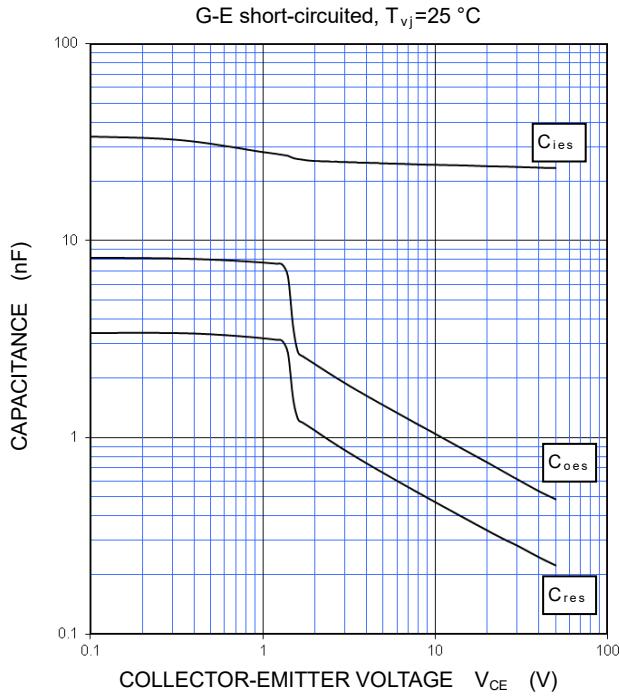
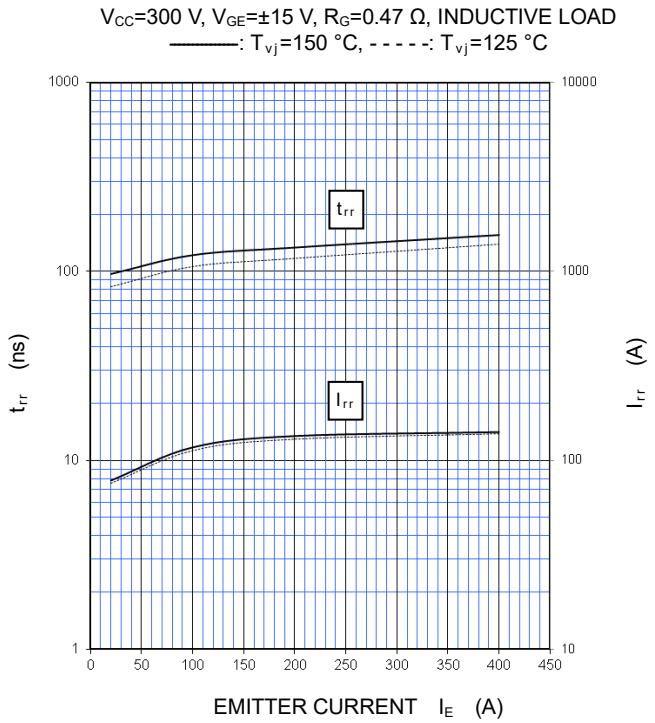
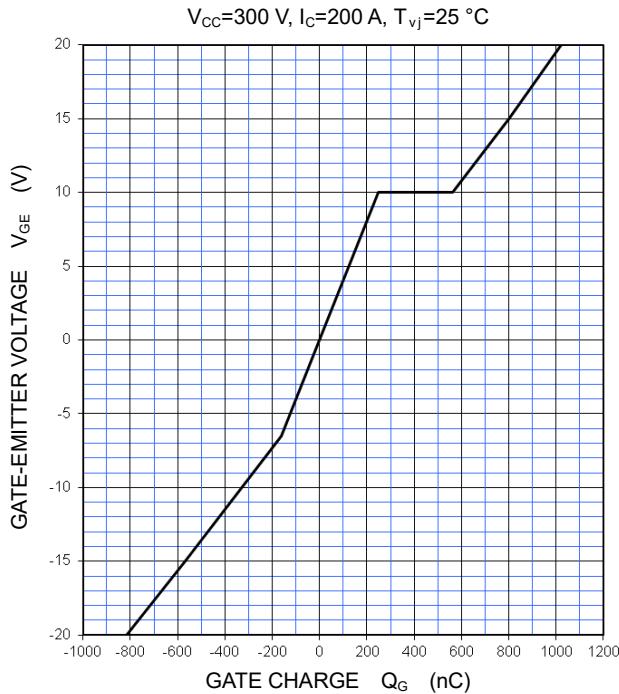
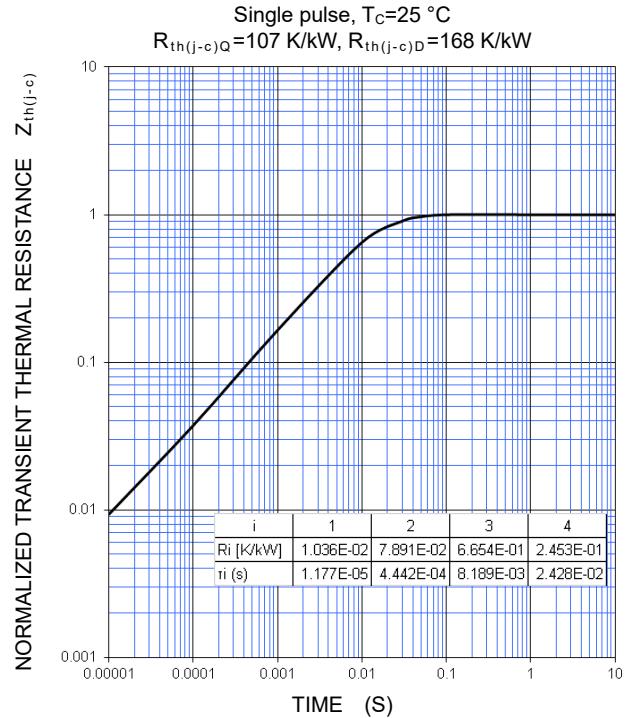
Di1

V_{EC} characteristics test circuit

Di2

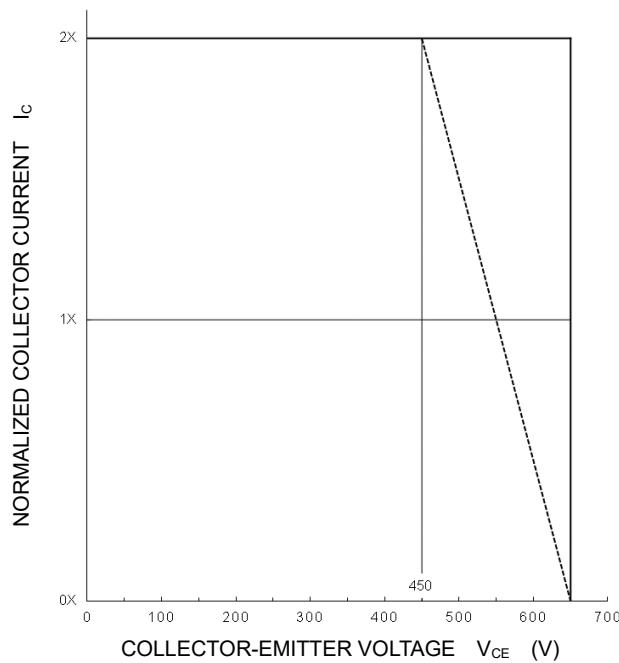
PERFORMANCE CURVES**OUTPUT CHARACTERISTICS
(TYPICAL)****COLLECTOR-EMITTER SATURATION VOLTAGE
CHARACTERISTICS
(TYPICAL)****COLLECTOR-EMITTER VOLTAGE CHARACTERISTICS
(TYPICAL)****FREE WHEELING DIODE
FORWARD CHARACTERISTICS
(TYPICAL)**

PERFORMANCE CURVES**HALF-BRIDGE SWITCHING CHARACTERISTICS
(TYPICAL)****HALF-BRIDGE SWITCHING CHARACTERISTICS
(TYPICAL)****HALF-BRIDGE SWITCHING CHARACTERISTICS
(TYPICAL)****HALF-BRIDGE SWITCHING CHARACTERISTICS
(TYPICAL)**

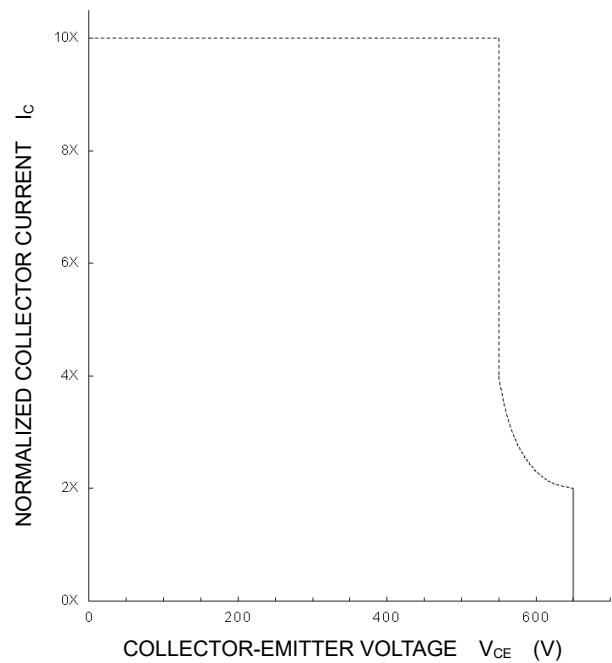
PERFORMANCE CURVES**CAPACITANCE CHARACTERISTICS
(TYPICAL)****FREE WHEELING DIODE
REVERSE RECOVERY CHARACTERISTICS
(TYPICAL)****GATE CHARGE CHARACTERISTICS
(TYPICAL)****TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS
(MAXIMUM)**

PERFORMANCE CURVES**TURN-OFF SWITCHING SAFE OPERATING AREA
(REVERSE BIAS SAFE OPERATING AREA)
(MAXIMUM)**

$V_{CC} \leq 450$ V, $V_{GE} = \pm 15$ V, $R_G = 0.47 \sim 33$ Ω ,
 —: $T_{vj} = 25 \sim 150$ $^{\circ}$ C (Normal load operations (Continuous))
 - - -: $T_{vj} = 175$ $^{\circ}$ C (Unusual load operations (Limited period))

**SHORT-CIRCUIT SAFE OPERATING AREA
(MAXIMUM)**

$V_{CC} \leq 400$ V, $V_{GE} = \pm 15$ V, $R_G = 0.47 \sim 33$ Ω ,
 $T_{vj} = 25 \sim 150$ $^{\circ}$ C, $t_W \leq 8$ μ s, Non-Repetitive



Note: The characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

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